

isc Silicon NPN Power Transistor
2SD1580
DESCRIPTION

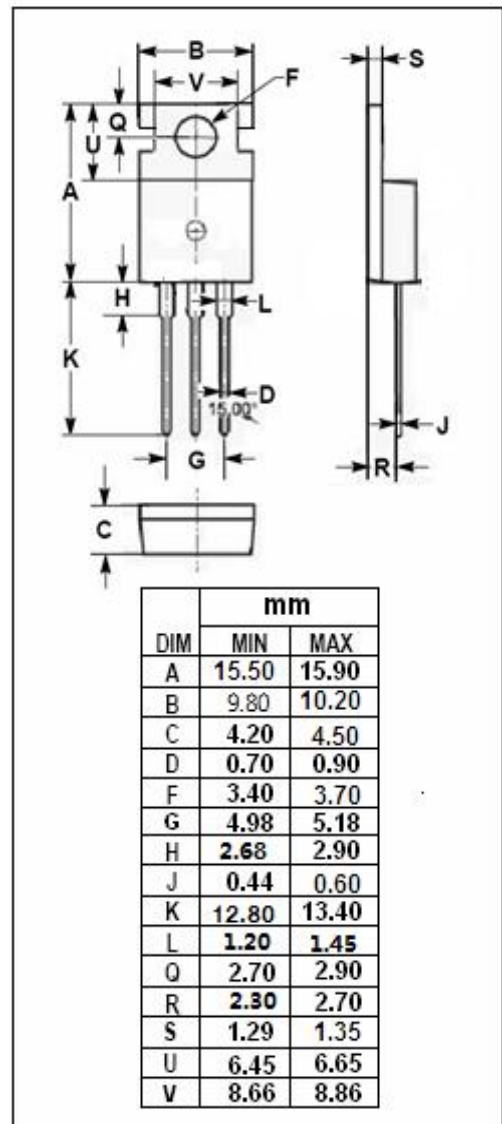
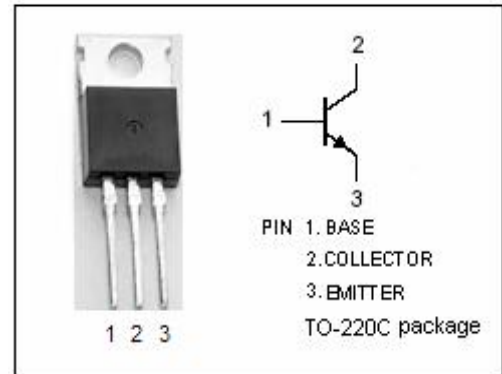
- Low Collector Saturation Voltage
: $V_{CE(sat)} = 1.0V(\text{Max.}) @ I_C = 4A$
- High Collector Power Dissipation
- Good Linearity of h_{FE}
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|--|---------|------------------|
| V_{CBO} | Collector-Base Voltage | 100 | V |
| V_{CEO} | Collector-Emitter Voltage | 80 | V |
| V_{EBO} | Emitter-Base Voltage | 5 | V |
| I_C | Collector Current-Continuous | 7 | A |
| I_{CM} | Collector Current-Pulse | 10 | A |
| P_C | Collector Power Dissipation @ $T_a = 25^\circ\text{C}$ | 1.5 | W |
| | Collector Power Dissipation @ $T_C = 25^\circ\text{C}$ | 40 | |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature Range | -55~150 | $^\circ\text{C}$ |



isc Silicon NPN Power Transistor
2SD1580
ELECTRICAL CHARACTERISTICS

 T_c=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|-----|------|-----|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 1mA; I _B = 0 | 80 | | | V |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | I _C = 50 μ A; I _E = 0 | 100 | | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = 50 μ A; I _C = 0 | 5 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 4A; I _B = 0.4A | | | 1.0 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 4A; I _B = 0.4A | | | 1.5 | V |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 100V; I _E = 0 | | | 10 | μ A |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 4V; I _C = 0 | | | 10 | μ A |
| h _{FE} | DC Current Gain | I _C = 1A; V _{CE} = 5V | 60 | | 320 | |
| f _T | Current-Gain—Bandwidth Product | I _E = -0.5A; V _{CE} = 5V | | 5 | | MHz |
| C _{OB} | Output Capacitance | I _E = 0; V _{CB} = 10V; f _{test} = 1.0MHz | | 150 | | pF |

◆ h_{FE} Classifications

| D | E | F |
|--------|---------|---------|
| 60-120 | 100-200 | 160-320 |

NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.